

# Outline

- **Preparation**
- Import Design & Floorplan
- Place & Power plan
- Clock Tree Synthesis
- Power Route & NanoRoute
- Save Out & Post-sim

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# Preparation

- **Copy your syn. files to syn/**
- **Adjust timing constraint in file:**
  - layout/lcd\_ctrl\_APR.sdc
  - set cycle 10
- **Select server with CentOS**
  - source innovus.cshrc
    - 請使用助教給的innovus.cshrc
- **\$ cd layout/**
- **\$ innovus**
  - **DON'T** use '&', we will use the terminal interface

```
├── layout
├── library
└── syn
    ├── lcd_ctrl_syn.sdf
    ├── lcd_ctrl_syn.v
    └── tsmc13_neg.v
```

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# Design import

- **File → Import Design → Load**
- **Load → xxx globals → Open**
- **Floorplan → IO Assignment File → **xxx.ioc****
- **OK**

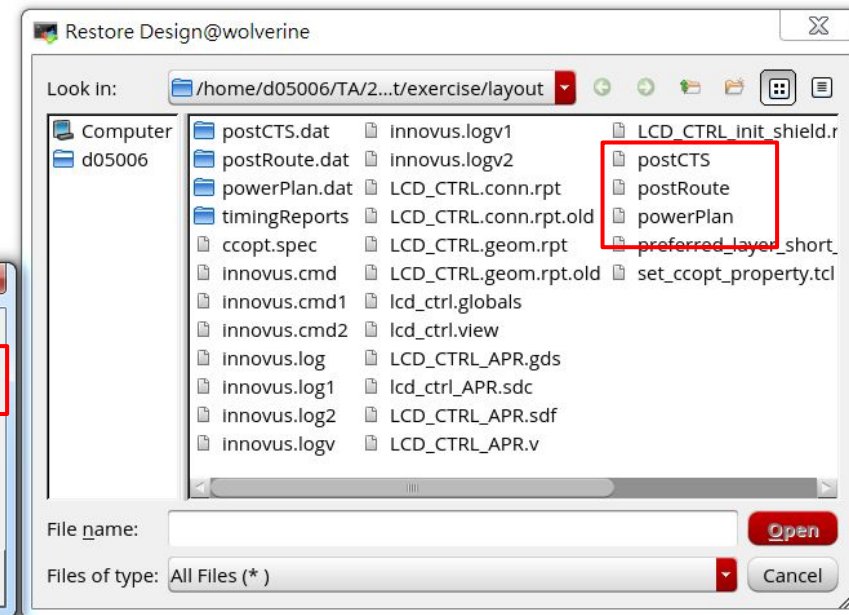
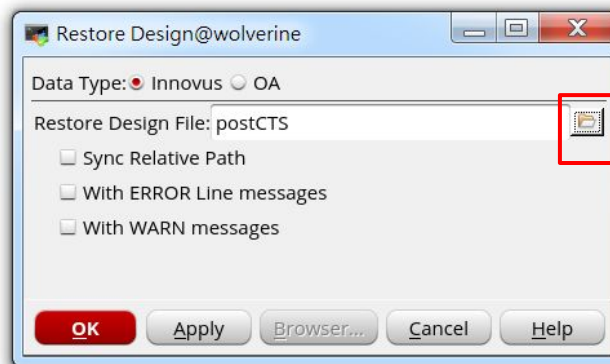
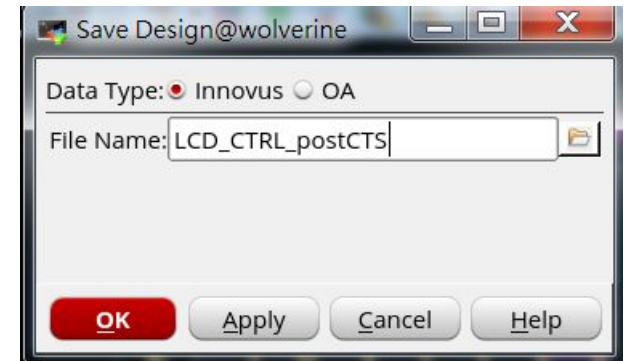
# Save/Load

## ■進行到任何步驟都可以儲存目前狀態

- File → Save Design
- 勾選‘Innovus’，輸入 File Name
- OK

## ■隨時中斷/不滿意可讀檔繼續步驟

- File → Restore Design
- 勾選 ‘Innovus’，按browse
- Open → OK



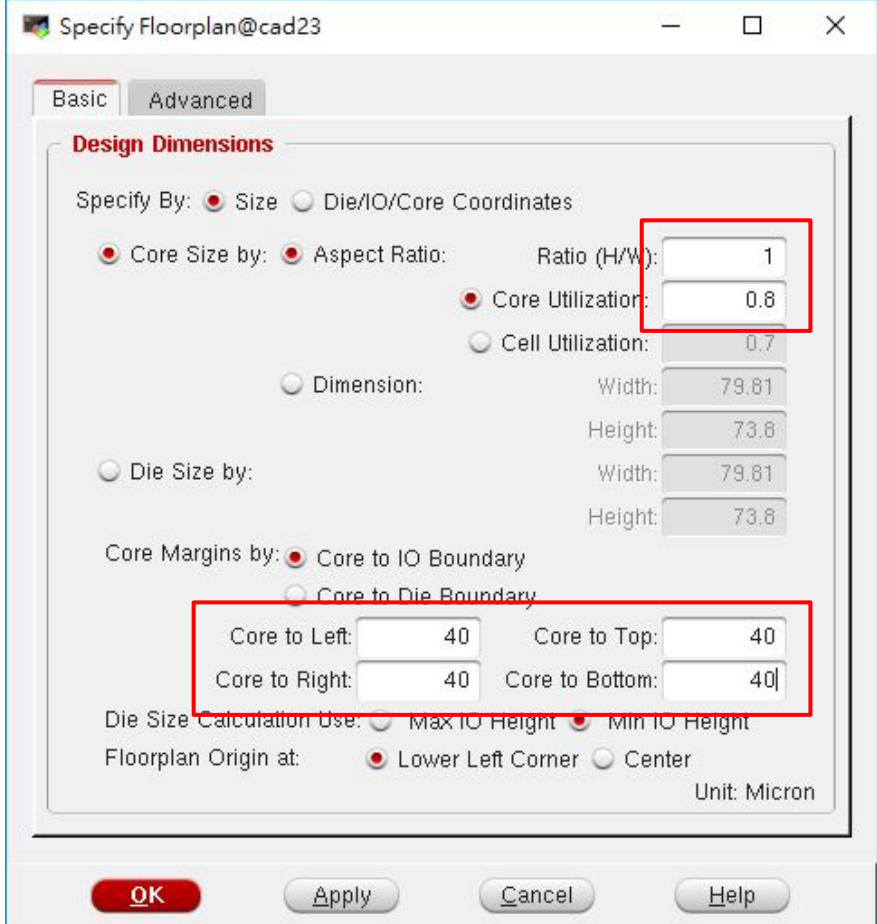
# Global Net Connect

- 目的:把所有的 Standard cell 的 power/ground pin 連接到 VDD/VSS
- Power → Connect Global Nets
  - Connect選Pin, Pin Name(s)填入VDD, Scope選Apply All, To Global Net填入VDD, 按Add to List
  - Connect選Pin, Pin Name(s)填入VSS, Scope選Apply All, To Global Net填入VSS, 按Add to List
  - 將1'b1/1'b0連接至VDD/VSS
    - Connect選Tie High, Scope選Apply All, To Global Net填入VDD, 按下Add to List
    - Connect選Tie Low, Scope選Apply All, To Global Net填入VSS, 按下Add to List
  - 按下Apply, 再按Check, 再關閉視窗

# Floorplan

## ■ Floorplan → Specify Floorplan

- 填入數值(可自行調整)
- OK



The image shows a screenshot of the 'Specify Floorplan' dialog box in a software application. The dialog has two tabs: 'Basic' and 'Advanced'. The 'Basic' tab is selected. The 'Design Dimensions' section is highlighted. It contains several options for specifying the floorplan dimensions. The 'Specify By' section has two radio buttons: 'Size' (selected) and 'Die/IO/Core Coordinates'. The 'Core Size by' section has two radio buttons: 'Aspect Ratio' (selected) and 'Dimension'. The 'Aspect Ratio' section has a 'Ratio (H/W):' field set to 1. The 'Core Utilization' section has two radio buttons: 'Core Utilization' (selected) and 'Cell Utilization'. The 'Core Utilization' field is set to 0.8. The 'Die Size by' section has two radio buttons: 'Die Size by' (selected) and 'Core Margins by'. The 'Die Size by' section has four fields: 'Width: 79.81', 'Height: 73.8', 'Width: 79.81', and 'Height: 73.8'. The 'Core Margins by' section has two radio buttons: 'Core to IO Boundary' (selected) and 'Core to Die Boundary'. The 'Core to IO Boundary' section has four fields: 'Core to Left: 40', 'Core to Top: 40', 'Core to Right: 40', and 'Core to Bottom: 40'. The 'Die Size Calculation Use' section has two radio buttons: 'Max IO Height' (selected) and 'Min IO Height'. The 'Floorplan Origin at' section has two radio buttons: 'Lower Left Corner' (selected) and 'Center'. The 'Unit: Micron' is indicated at the bottom right. The 'OK' button is highlighted in red.

Specify Floorplan@cad23

Basic Advanced

**Design Dimensions**

Specify By: ☒ Size ☐ Die/IO/Core Coordinates

☒ Core Size by: ☒ Aspect Ratio: Ratio (H/W):

☒ Core Utilization:

☐ Cell Utilization:

☐ Dimension: Width:  Height:

☐ Die Size by: Width:  Height:

Core Margins by: ☒ Core to IO Boundary ☐ Core to Die Boundary

Core to Left:  Core to Top:

Core to Right:  Core to Bottom:

Die Size Calculation Use: ☐ Max IO Height ☒ Min IO Height

Floorplan Origin at: ☒ Lower Left Corner ☐ Center

Unit: Micron

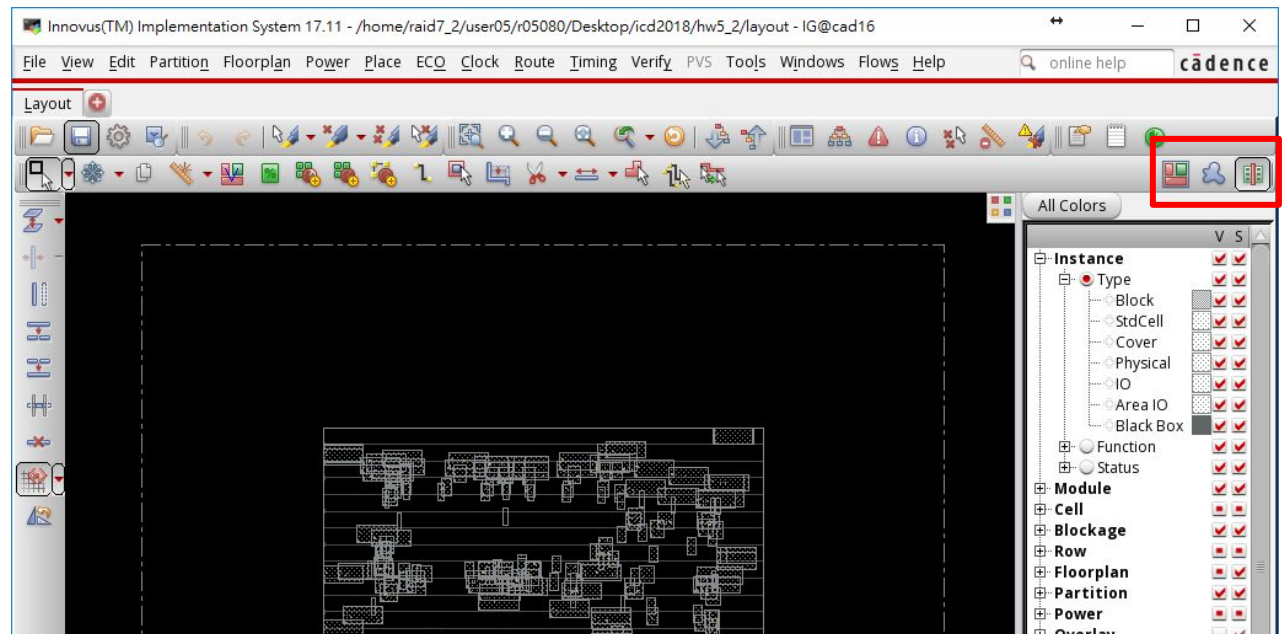
OK Apply Cancel Help



# Placement In Floorplan Mode

## ■ Place → Place Standard Cell

- 選擇Run Placement In Floorplan Mode (Optimization Options的選項取消勾選: Include Pre-Place Optimization, 按OK
- 執行完之後可以選擇不同的design view (下圖紅框處), 會看到tool已經幫我們把所有的cell擺進去core裡面



# Timing analysis

## ■ Timing → Report Timing

- Design Stage選擇Pre-Place, 按下OK
  - 此時Tool會開始分析trial route與RC Extraction, 計算出各點的delay後再使用STA (Static timing analysis)分析Data path
  - Tool跑完之後可以在Terminal看到分析之後的結果, 主要是WNS (Worst Negative Slack), 如果這個值是負的, 則表示目前的Placement結果無法達到lcd\_ctrl\_APR.sdc裡面的Timing constraint
  - 如果WNS是負的, Innovus有補救的方法, 就是執行Timing Optimization (後面會講解步驟, 這裡先不用做)

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# Full mode place

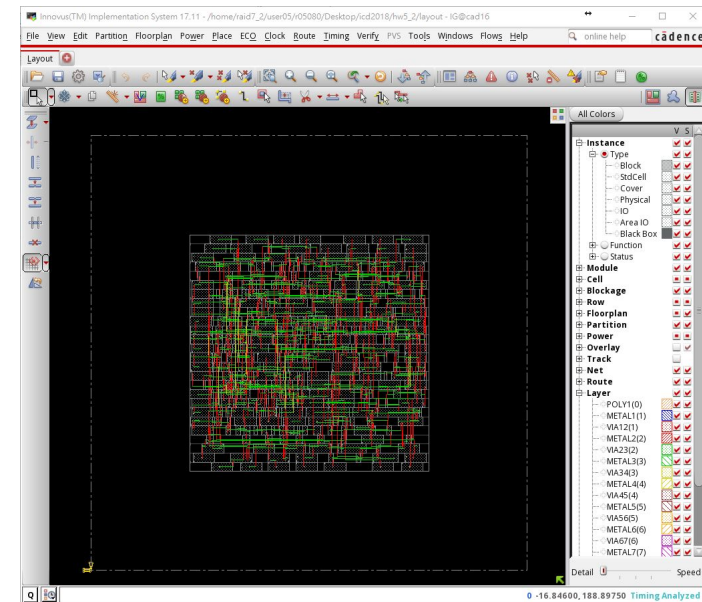
## ■ Place → Place Standard Cell

- 選擇Run Full Placement, 取消Include Pre-Place Optimization
- 按Mode, 加選Enable Clock Gating Awareness, 按OK
- 按OK開始跑Placement

## ■ 執行Place → Refine Placement來讓cell擺置的方向正確

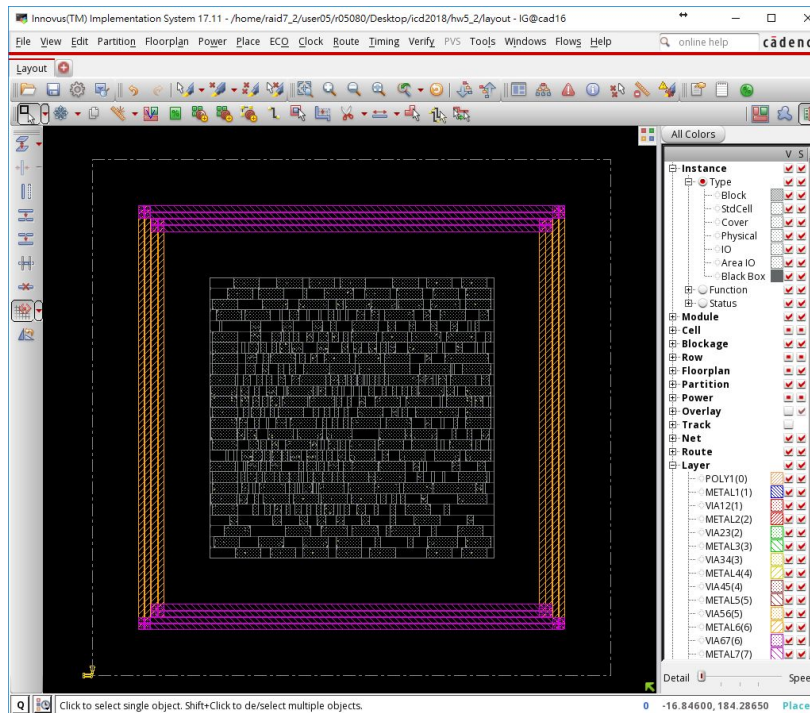
## ■ Timing → Report Timing

- Design Stage選擇Pre-CTS
- 如果WNS為負, 則進行Timing Optimization
  - ECO → Optimize Design
  - Design Stage選擇Pre-CTS, 按OK



# Power ring

- 目的:在core周圍建立一圈Power ring, 讓晶片內部供電電壓均勻, 避免IR drop
- Place → Refine Placement , 直接按OK
  - 此步驟主要是先拿掉timing analysis產生的trial route的結果, 以免影響Powerplan, 做完這步之後會發現Physical view裡面原本有的繞線都被移除了



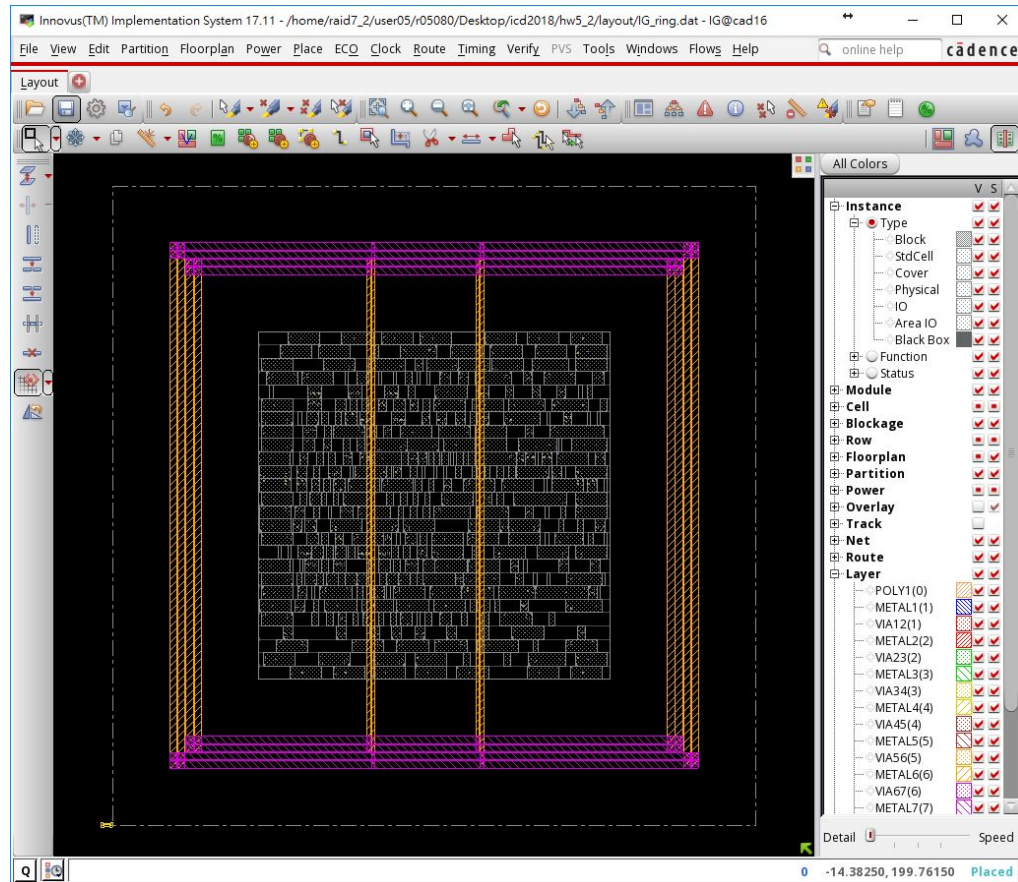
# Power ring

## ■ Power → Power Planning → Add Ring

- Net(s)選VDD VSS
- Ring Configuration
  - Top/Bottom Layer改成METAL7 H
  - Left/Right Layer改成METAL6 V
  - Width都改成2
  - 填完之後按一下Spacing下面的Update
  - 勾選Offset: Center in channel
- 切換到Advanced
  - 勾選wire group
  - 勾選Interleaving
  - Number of bits填入2, 按OK
- 做完之後可以看到Core跟I/O Pad之間多了一圈Power ring

# Power stripe

- 目的: 加入垂直方向的Power stripe, 也是用來使core内部的供電電壓均勻



# Power stripe

## ■ Power → Power Planning → Add Stripe

- Net(s) 選VDD VSS
- Layer選擇METAL6 (由於我們想要create的是直的stripe, 所以在這裡我們選擇METAL6, 若是要打上橫的stripe, 則選擇METAL7)
- Width設定為1, 按下Update
- 選擇Set-to-set distance, 並設定為30
- 下方First/Last Stripe 的start設定為30, Stop設定為30
- 切換到Advanced
  - 勾選Switch layer over obstructions
  - 勾選wire group與Interleaving, Number of bits設定為1
- 按OK



# DRC Check

## ▪ Verify → Verify DRC, 按OK

- 也可以選擇直接在terminal輸入verifyGeometry指令作為替代
- 看terminal是否有任何的Violations, 在這裡出現的Violation最好要解決掉(可以重新做placement或是手動移動block), 否則留到後面就很難解決了
- 在layout上面如果有出現X的圖案, 則表示那邊有DRC error

# Add Tie High/Low Cell

## ■先做一下timing analysis

- Timing → Report Timing
- Design Stage選擇Pre-CTS, 按下OK
- 若 WNS是負的, 則必須做 optimization, 或是DRC有max fanout violation 也可以用optimization來修
  - ECO → Optimize Design, 在Optimization Type裡加選Max Fanout, OK
  - 如果Optimization作完後仍然WNS為負, 則加選Incremental繼續執行 Optimization, 直到修到WNS為正

# Add Tie High/Low Cell

## ■將1'b0及1'b1連到tie high或tie low cell上

- 執行 Place → Tie Hi/Lo Cell → Add → Mode, 左欄選 TieHiLo, Cell Name 輸入TIEHI TIELO, 勾選Specify Maximum Fanout 設 10, 勾選 Specify Maximum Distance設100, OK。
- Cell Name已設為TIEHI TIELO, OK (TIEHI TIELO 中間有空格, 外面不要有大括號)

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# Clock Tree Synthesis (CTS)

- 本步驟都在terminal輸入指令
- 設定ccopt的基本參數, 助教已經帮大家寫好直接source就好
  - `$ source set_ccopt_property.tcl`
- 根據lcd\_ctrl\_APR.sdc檔產生對應的ccopt參數
  - `$ create_ccopt_clock_tree_spec -file ccopt.spec`
  - `$ source ccopt.spec`
- 進行Clock Tree Synthesis
  - `$ ccopt_design -cts`

# Post-CTS Timing analysis

- **Timing → Report Timing, Design Stage 選 Post-CTS, Analysis Type 選 Setup, OK**
  - 若 WNS 是負的, 做 ECO → Optimize Design..., 選 Post-CTS, OK
  - 重複直到 WNS 為正
- **Timing → Report Timing, Design Stage 選 Post-CTS, Analysis Type 選 Hold, OK。**
  - 若 WNS 是負的, 做 ECO → Optimize Design..., 選 Post-CTS, OK
  - 重複 11.4 直到 WNS 為正

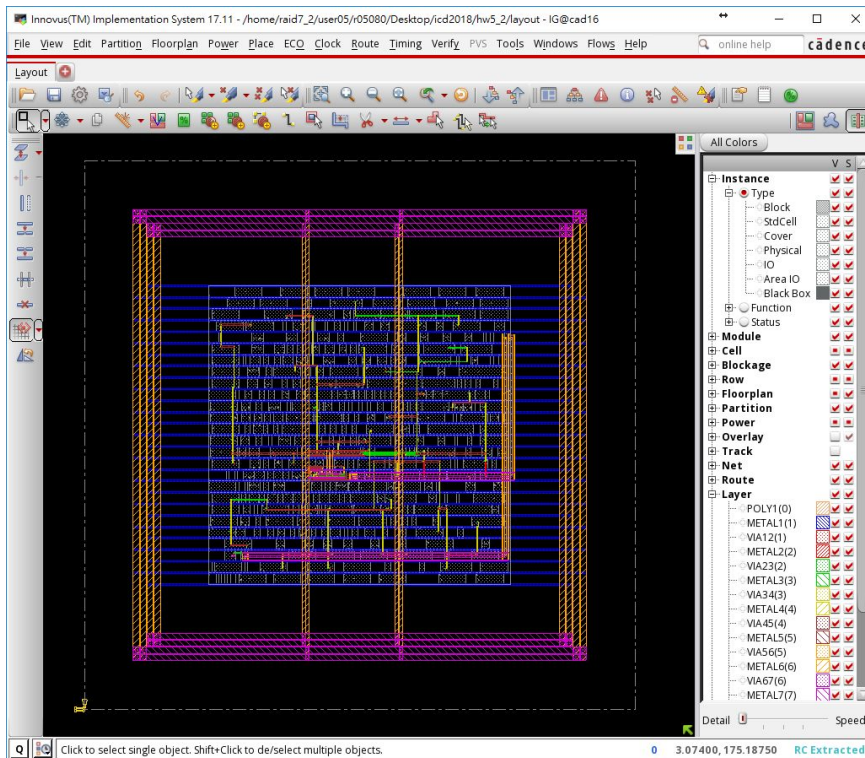
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# Route Power

## ▪Route →Special Route

- Basic → Net(s) → ...→加入 VSS VDD
- SRoute 只留下 Follow pins → OK
- 可以看到core cell的power(藍色的線) 都連到左右的power ring上





# 檢查 Special Net 的 DRC 及 connectivity

## ▪ Place → Refine Placement, OK

- 將 trial route 的 signal net 移除

## ▪ Verify Connectivity, Net type 選 Special Only, Check 取消 unrouted net, OK

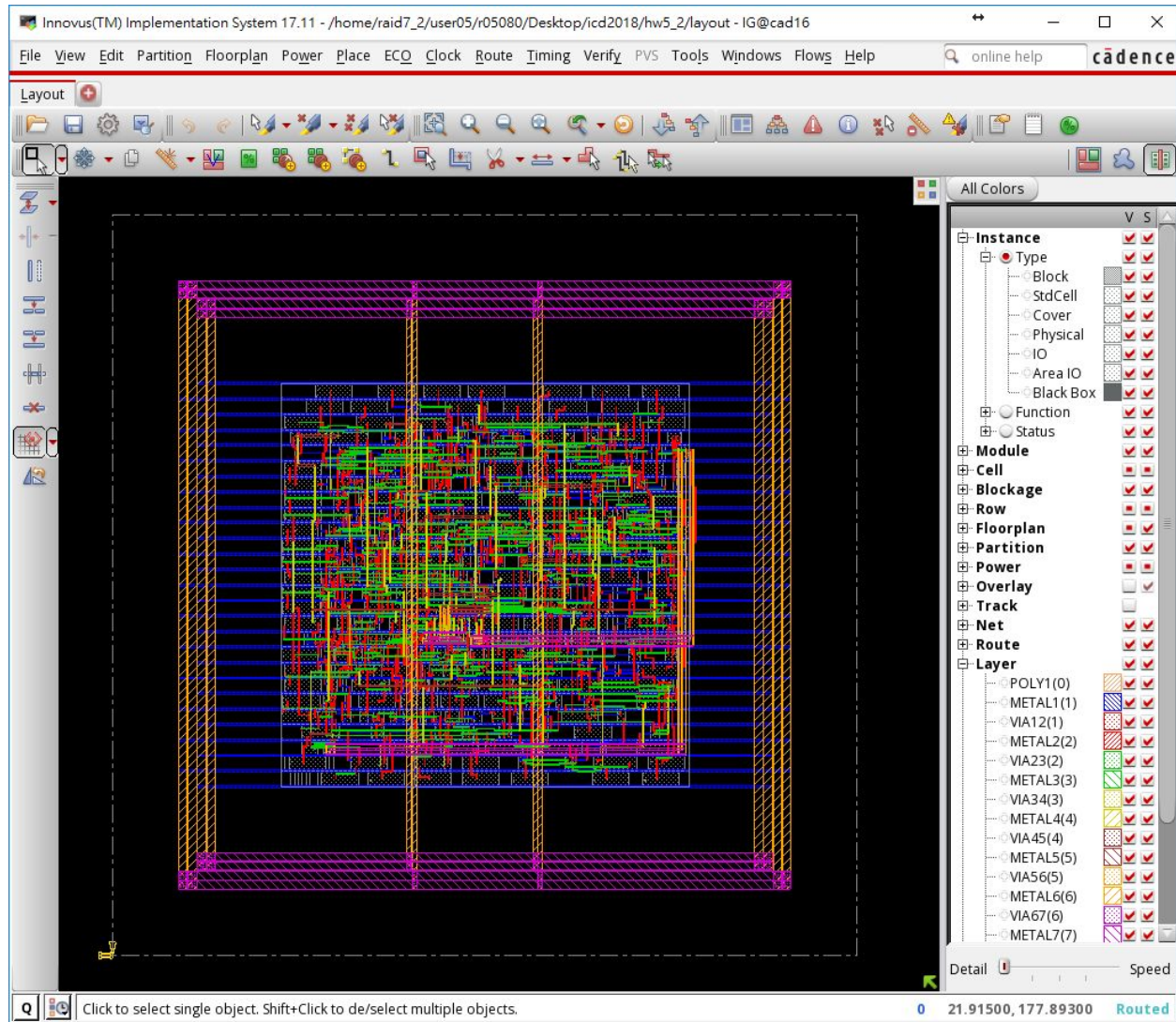
- 如果有任何的 violation, 每一個都用滑鼠點擊選取 violation 的繞線, 按鍵盤大寫T以修正問題
- 修正完後可以重複本投影片確認不再有 violation

# Routing

## ▪Route→NanoRoute→Route

- 勾選Insert Diodes, Diode Cell Name輸入ANTENNA
- 勾選Timing driven
- 勾選SI Driven
- 按OK右邊的Attribute
  - 選 Nettype(s), Clock Nets
  - Weight: 10
  - Spacing: 1
  - Avoid Detour: True (意思是 Route as short as possible)
  - 按 OK
- 按OK, 開始routing, 看看有沒有violation

# Routing



# Post route Timing Analysis

## ■在terminal輸入指令

- \$ setAnalysisMode -analysisType onChipVariation

## ■Timing → Report Timing

- Design Stage 選 Post-Route, Analysis Type: Setup, OK
- 若 WNS 為負的則：
  - Optimize → Optimize Design, Design Stage選Post-route, 加選Max Fanout, OK。一直重覆到WNS為正的為止
- Design Stage 選 Post-Route, Analysis Type: Hold, OK

# DRC Check

- **Verify → Verify DRC , 按OK**

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# Finish

## ■ Generate files for post-sim

- File→Save →Netlist...
  - Netlist File 填 lcd\_ctrl\_APR.v, OK
  - Timing→Write SDF
    - » 取消 Ideal Clock, SDF Output File 填 lcd\_ctrl\_APR.sdf, OK

## ■ Generate area report

- File→Report→Summary...
  - 選 Text Only, 檔名為 summaryReport.rpt, OK
    - » 通常會以 Total area of Core

# Finish

## ■ Stream out GDS

- Tool → Set Mode → Mode Setup
  - 左欄選StreamOut, 取消Virtual Connection, OK
- File → Save → GDS/OASIS
  - Output File填入lcd\_ctrl\_APR.gds
  - Map File填入 ../library/streamOut.map
  - 勾選Merge File, 填入 ../library/gds/tpz013g3\_v1.1.gds 和 ../library/gds/tsmc13gfsg\_fram.gds (兩個檔案用空格隔開)
  - 勾選Write abstract information for LEF Macros, Unit: 1000
  - OK

## ■ 可關閉Innovus



# Post-layout simulation

## ▪ Check your APR Verilog netlist (2 way)

- `$ vcs <test bench> <apr netlist> ./syn/tsmc13_neg.v -full64 -R +neg_tchk +maxdelays -debug_access+all +v2k`
- 如果模擬沒過，可以慢慢提高testbench中的cycle time，直到通過為止

```
Warning! Timing violation
$setuphold<setup>( posedge CLK:12 NS, posedge CEN:11960 PS,  1.00 : 1 NS,  0.50 : 500 PS );
File: ./IROM.v, line = 326
Scope: test.IROM_1.irom_1
Time: 12 NS

Warning! Timing violation
$setuphold<setup>( posedge CLK &&& re_flag:12 NS, posedge WEN:11452 PS,  1.00 : 1 NS,  0.50 : 500 PS );
File: ./IRB.v, line = 419
Scope: test.IRB_1
Time: 12 NS

Warning! Timing violation
$setuphold<setup>( posedge CLK &&& re_flag:12 NS, negedge A[5]:11552 PS,  1.00 : 1 NS,  0.50 : 500 PS );
File: ./IRB.v, line = 432
Scope: test.IRB_1
Time: 12 NS
```

# Some common problems

- **Clock cycle in transistor level simulation should be consistent with synthesis and layout step**
- **Remember to select APR.sdf/.v file instead of syn.sdf/.v file when performing transistor level simulation**
- **You should redo the **synthesis** process if you want to relax the timing constraint**
- **What can I do when simulation fail?**
  - Make sure all the Verilog and SDF file, relative path and linking are correct
  - Relax the timing constraint and repeat synthesis and layout
  - You may try 2x constraint cycle time when running simulation
  - Open nWave and debug